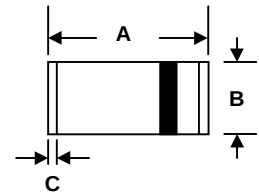


LL-34(Mini-melf) Glass Switching Diode

Features

- Fast Switching Device (TRR <50 nS)
- Power Dissipation of 400mW
- High Stability and High Reliability
- Low reverse leakage



Mechanical Data

- LL-34 Glass Case
- Color band denotes cathode end
- Mounting Position: Any

MiniMELF		
Dim	Min	Max
A	3.30	3.60
B	1.40	1.50
C	0.25	0.33
All Dimensions in mm		

Maximum Ratings & Thermal Characteristics (Ratings at 25°C ambient temperature unless otherwise specified.)

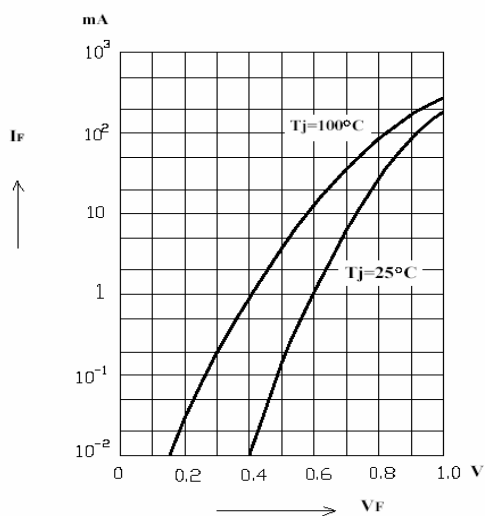
Paramet	Symbol	Value				Unit
		BAV100	BAV101	BAV102	BAV103	
Reverse Voltage	V_R	50	100	150	200	V
Maximum Repetitive Reverse Voltage	V_{RRM}	60	120	200	250	V
Power Dissipation	P_d	400				mW
Operating junction temperature	T_j	175				°C
Storage temperature range	T_s	-65~+175				°C
Forward DC Current at ($T_A = 25^\circ\text{C}$)	I_F	250				mA
Average Forward Current($T_A=25^\circ\text{C}$ & $f \geq 50\text{Hz}$)	$I_{F(AV)}$	200				mA
Repetitive Peak Forward Current	I_{FRM}	625				mA
Peak Forward Surge Current @ $t_p=1\text{s}$; $T_A=25^\circ\text{C}$	I_{FSM}	1.0				A

Electrical Characteristics (Ratings at 25°C ambient temperature unless otherwise specified).

Symbols	Parameter		Test Condition	Limits		Unit
				Min	Max	
I_R	Leakage Current	BAV100	$V_R=50\text{V}$; $T_j=25^\circ\text{C}$	---	100	nA
		BAV101	$V_R=100$; $T_j=25^\circ\text{C}$			
		BAV102	$V_R=150$; $T_j=25^\circ\text{C}$			
		BAV103	$V_R=200$; $T_j=25^\circ\text{C}$			
V_F	Forward Voltage	$I_F=100\text{mA}$		---	1.00	V
		$I_F=200\text{mA}$			1.25	
TRR1	Reverse Recovery Time	$I_F = 30\text{mA}$ to $I_R = 30\text{mA}$, $I_{rr} = 3\text{mA}$, $R_L = 100$.		---	50	nS
Ctot	Total Capacitance	at $V_R = 0$, $f = 1\text{MHz}$		---	1.5	pF
rf	Dynamic Forward Resistance	$I_F=10\text{mA}$		5		Ω

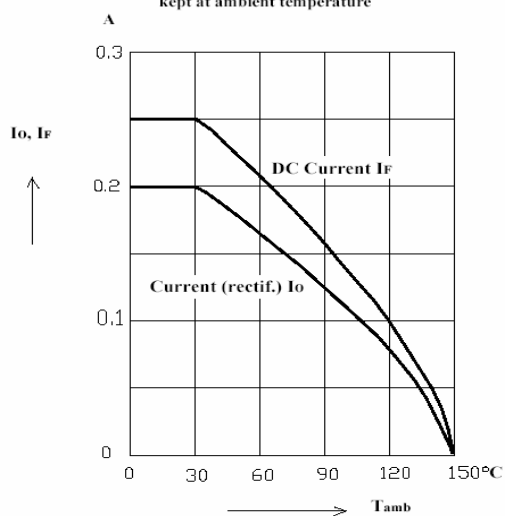
Characteristic Curves

Forward characteristics

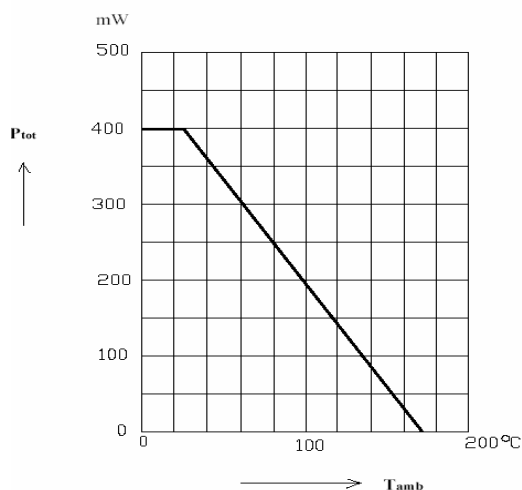


Admissible forward current versus ambient temperature

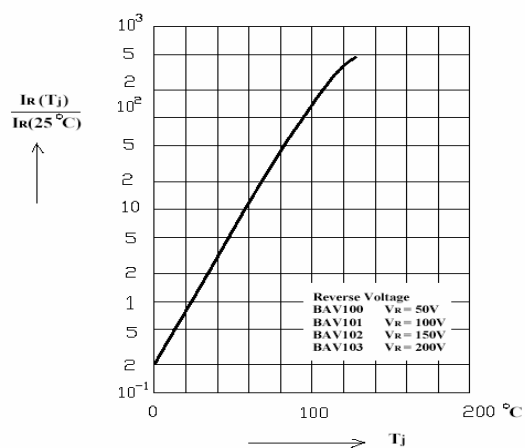
Valid provided that electrodes are kept at ambient temperature



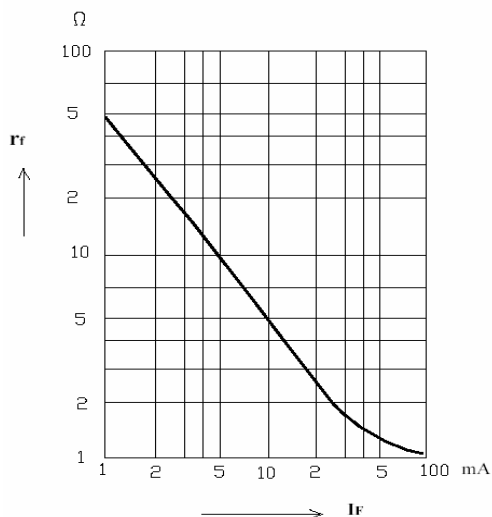
Admissible power dissipation versus ambient temperature



Leakage current versus junction temperature



Dynamic forward resistance versus forward current



Capacitance versus reverse voltage

